

## FGA10 InGaAs Photodiode

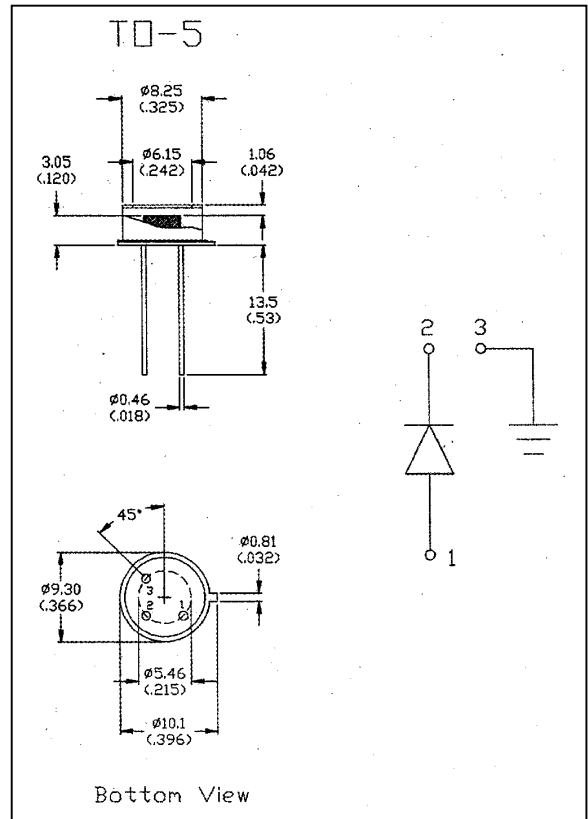
- High Responsivity
- Low Capacitance: High Speed

### Electrical Characteristics

Spectral Response:	800-1800nm*****
Active Diameter:	1.0mm
Rise/Fall Time (RL=50Ω):	5.0ns (5V)
Bandwidth (RL=50Ω, -3dB,5V):	40 MHz min
NEP@1550nm:	1*10 <sup>-14</sup> W/√Hz min
Dark Current:	100nA max (25nA typ) @ 5V
Package:	TO-5

### Maximum Ratings

Damage Threshold CW:	100mW
Max Bias Voltage:	20V
Storage Temperature:	-40 to 125° C
Operating Temperature:	-40 to 85° C
Reverse Current:	10mA
Forward Current:	10mA



The Thorlabs FGA10 photodiode is ideal for measuring both pulsed and CW light sources, by converting the optical power to an electrical current. The InGaAs detector is housed in a TO-5 package with an anode, cathode and case connection. The photodiode anode produces a current which is a function of the incident light power and the wavelength. The responsivity  $\mathfrak{R}(\lambda)$ , can be read from Figure 1 to estimate the amount of photocurrent to expect. This can be converted to a voltage by placing a load resistor ( $R_{LOAD}$ ) from the photodiode anode to the circuit ground. The output voltage is derived as:

$$V_o = P * \mathfrak{R}(\lambda) * R_{LOAD}$$

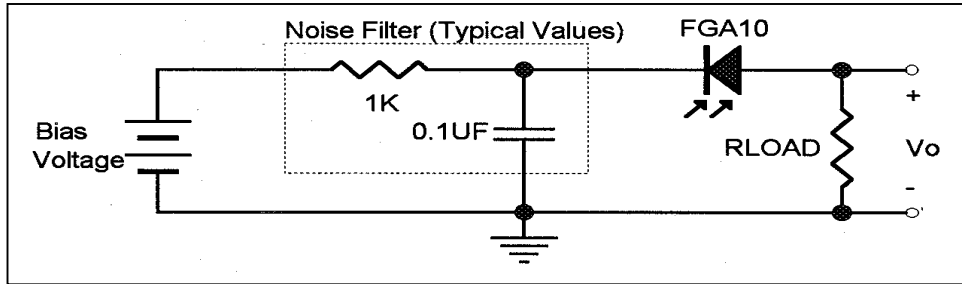
The bandwidth,  $f_{BW}$ , and the rise time response,  $T_R$ , are determined from the diode capacitance,  $C_J$ , and the load resistance,  $R_{LOAD}$ , as shown below. The diode capacitance can be lowered by placing a bias voltage from the photodiode cathode to the circuit ground. The effect of the bias voltage vs. Diode capacitance can be read from Figure 2.

$$f_{BW} = 1/(2\pi * R_{LOAD} * C_J), T_R = 0.35/f_{BW}$$

### Related Thorlabs Products

FDS010, FDS100, PDA55, PDA155, PDA255, PDA400, WS02, TM2448

## Typical Circuit Diagram



## Typical Plots

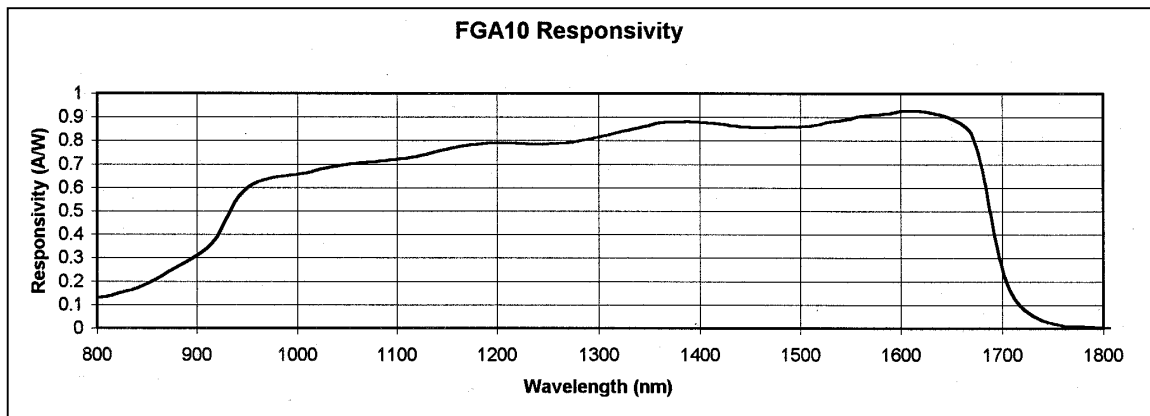


Figure 1

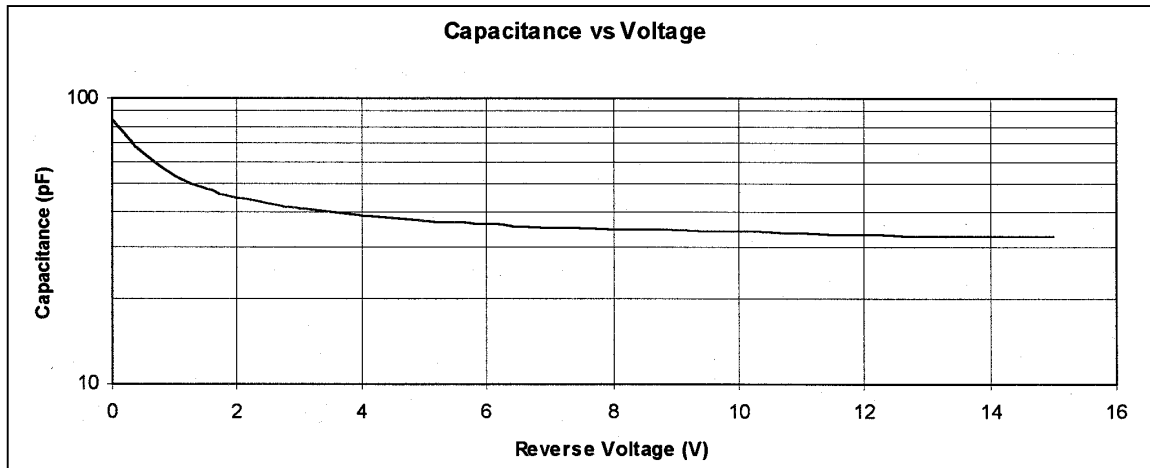


Figure 2